## Description

Semicoa Semiconductors offers:

- Screening and processing per MIL-PRF-19500 Appendix E
- JAN level (2N2857J)
- JANTX level (2N2857JX)
- JANTXV level (2N2857JV)
- JANS level (2N2857JS)
- QCI to the applicable level
- $100 \%$ die visual inspection per MIL-STD-750 method 2072 for JANTXV and JANS
- Radiation testing (total dose) upon request

Please contact Semicoa for special configurations www.SEMICOA.com or (714) 979-1900

## Applications

- Ultra-High frequency transistor
- Low power
- NPN silicon transistor



## Features

- Hermetically sealed TO-72 metal can
- Also available in chip configuration
- Chip geometry 0011
- Reference document:

MIL-PRF-19500/343

## Benefits

- Qualification Levels: JAN, JANTX, JANTXV and JANS
- Radiation testing available $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ unless otherwise specified


## Absolute Maximum Ratings

| Parameter | Symbol | Rating | Unit |
| :--- | :---: | :---: | :---: |
| Collector-Emitter Voltage | $\mathrm{V}_{\mathrm{CEO}}$ | 15 | Volts |
| Collector-Base Voltage | $\mathrm{V}_{\mathrm{CBO}}$ | 30 | Volts |
| Emitter-Base Voltage | $\mathrm{V}_{\mathrm{EBO}}$ | 3 | Volts |
| Collector Current, Continuous | $\mathrm{I}_{\mathrm{C}}$ | 40 | mA |
| Power Dissipation, $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | $\mathrm{P}_{\mathrm{T}}$ | 200 | mW |
| Derate linearly above $25^{\circ} \mathrm{C}$ | $\mathrm{P}_{\mathrm{T}}$ | 1.14 | $\mathrm{~mW} /{ }^{\circ} \mathrm{C}$ |
| Power Dissipation, $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ | $\mathrm{T}_{\mathrm{J}}$ | $\mathrm{mW0}$ | $\mathrm{~mW} /{ }^{\circ} \mathrm{C}$ |
| Derate linearly above $25^{\circ} \mathrm{C}$ | $\mathrm{T}_{\mathrm{STG}}$ | -65 to +200 | ${ }^{\circ} \mathrm{C}$ |
| Operating Junction Temperature |  | -65 to +200 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature |  |  |  |

## ELECTRICAL CHARACTERISTICS

## Off Characteristics

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Units |
| :--- | :---: | :--- | :---: | :---: | :---: | :---: |
| Collector-Emitter Breakdown Voltage | $\mathrm{V}_{(\mathrm{BR}) \mathrm{CEO}}$ | $\mathrm{I}_{\mathrm{C}}=3 \mathrm{~mA}$ | 15 |  |  | Volts |
| Collector-Base Cutoff Current | $\mathrm{I}_{\mathrm{CBO} 1}$ | $\mathrm{~V}_{\mathrm{CB}}=15$ Volts |  |  | 10 | nA |
| Collector-Base Cutoff Current | $\mathrm{I}_{\mathrm{CBO} 3}$ | $\mathrm{~V}_{\mathrm{CB}}=30$ Volts |  | 1 | $\mu \mathrm{~A}$ |  |
| Collector-Base Cutoff Current | $\mathrm{I}_{\mathrm{CBO} 2}$ | $\mathrm{~V}_{\mathrm{CB}}=15$ Volts, $\mathrm{T}_{\mathrm{A}}=150^{\circ} \mathrm{C}$ |  |  | 1 | $\mu \mathrm{~A}$ |
| Collector-Emitter Cutoff Current | $\mathrm{I}_{\mathrm{CES}}$ | $\mathrm{V}_{\mathrm{CE}}=16$ Volts |  |  |  |  |
| Emitter-Base Cutoff Current | $\mathrm{I}_{\mathrm{EBO} 1}$ | $\mathrm{~V}_{\mathrm{EB}}=3$ Volts |  | 100 | nA |  |

On Characteristics Pulse Test: Pulse Width = 300 $\mu \mathrm{s}$, Duty Cycle $\leq 2.0 \%$

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Units |
| :--- | :---: | :--- | :---: | :---: | :---: | :---: |
| DC Current Gain | $\mathrm{h}_{\text {FE1 }}$ <br> $\mathrm{h}_{\mathrm{FE} 2}$ | $\mathrm{I}_{\mathrm{C}}=3 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=1$ Volts <br> $\mathrm{I}_{\mathrm{C}}=3 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=1$ Volts | 30 <br> $\mathrm{~T}_{\mathrm{A}}=-55^{\circ} \mathrm{C}$ |  | 150 |  |
| Base-Emitter Saturation Voltage | $\mathrm{V}_{\text {BEsat }}$ | $\mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=1 \mathrm{~mA}$ |  |  | 1.0 | Volts |
| Collector-Emitter Saturation Voltage | $\mathrm{V}_{\text {CEsat }}$ | $\mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=1 \mathrm{~mA}$ |  |  | 0.4 | Volts |

## Dynamic Characteristics

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Units |
| :--- | :---: | :---: | :---: | :---: | :---: | :---: |
| Magnitude - Common Emitter, Short <br> Circuit Forward Current Transfer Ratio | $\mathrm{h}_{\mathrm{FE}}$ | $\mathrm{V}_{\mathrm{CE}}=6 \mathrm{Volts}, \mathrm{I}_{\mathrm{C}}=5 \mathrm{~mA}$, <br> $\mathrm{f}=100 \mathrm{MHz}$ | 10 |  | 21 |  |
| Small Signal Short Circuit Forward <br> Current Transfer Ratio | $\mathrm{h}_{\mathrm{FE}}$ | $\mathrm{V}_{\mathrm{CE}}=6 \mathrm{Volts}, \mathrm{I}_{\mathrm{C}}=2 \mathrm{~mA}$, <br> $\mathrm{f}=1 \mathrm{kHz}$ | 50 |  | 220 |  |
| Collector to Base Feedback <br> Capacitance | $\mathrm{C}_{\mathrm{CB}}$ | $\mathrm{V}_{\mathrm{CB}}=10 \mathrm{Volts}, \mathrm{I}_{\mathrm{E}}=0 \mathrm{~mA}$, <br> $100 \mathrm{kHZ}<\mathrm{f}<1 \mathrm{MHz}$ |  | 1 | pF |  |
| Collector Base time constant | $\mathrm{r}_{\mathrm{b}} \mathrm{C}_{\mathrm{C}}$ | $\mathrm{V}_{\mathrm{CB}}=6 \mathrm{Volts}, \mathrm{I}_{\mathrm{E}}=2 \mathrm{~mA}$, <br> $\mathrm{f}=31.9 \mathrm{MHz}$ | 4 |  | 15 | ps |
| Small Signal Power Gain | $\mathrm{G}_{\mathrm{pe}}$ | $\mathrm{V}_{\mathrm{CE}}=6 \mathrm{Volts}, \mathrm{I}_{\mathrm{E}}=1.5 \mathrm{~mA}$, <br> $\mathrm{f}=450 \mathrm{MHz}$ | 12.5 |  | 21 | MHz |
| Noise Figure | F | $\mathrm{V}_{\mathrm{CE}}=6 \mathrm{Volts}, \mathrm{I}_{\mathrm{C}}=1.5 \mathrm{~mA}$, <br> $\mathrm{f}<450 \mathrm{MHz}, \mathrm{R}_{\mathrm{g}}=50 \Omega$ |  |  | 4.5 | dB |

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